

Date: 5th Sept, 2017

Data Sheet Issue: A1

Rectifier Diode Module Types W9830TJ120MBR & W9830TJ150MBR

Absolute Maximum Ratings

V _{RRM} [V]	Types
1200	W9830TJ120MBR
1500	W9830TJ150MBR

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{RRM}	Repetitive peak reverse voltage 1)	1200-1500	V
V_{RSM}	Non-repetitive peak reverse voltage 1)	1300-1600	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{F(AV)M}$	Maximum average forward current, T _c =55°C ²⁾	4020	Α
$I_{F(AV)M}$	Maximum average forward current, T _c =100°C ²⁾	2980	Α
$I_{F(AV)M}$	Maximum average forward current. T _c =85°C ²⁾	3345	Α
I _{F(RMS)M}	Nominal RMS forward current, T _c =25°C ²⁾	7280	Α
I _{T(d.c.)}	D.C. forward current, T _c =25°C	5850	Α
I _{FSM}	Peak non-repetitive surge t _p =10ms, V _{rm} =60%V _{RRM} ³⁾	72	kA
I _{FSM2}	Peak non-repetitive surge t _p =10ms, V _{rm} ≤10V ³⁾	80	kA
I ² t	I ² t capacity for fusing t _p =10ms, V _{rm} =60%V _{RRM} ³⁾	25.9×10 ⁶	A ² s
I ² t	I²t capacity for fusing t _p =10ms, V _{rm} ≤10V ³)	32×10 ⁶	A ² s
V _{ISOL}	Isolation Voltage 4)	3000	V
T _{vj op}	Operating temperature range	-40 to +190	°C
T_{stg}	Storage temperature range	-55 to +190	°C

Notes:

- 1) De-rating factor of 0.13% per °C is applicable for T_{vj} below 25°C.
- 2) Single phase; 50 Hz, 180° half-sinewave.
- 3) Half-sinewave, 190°C T_{vj} initial.
- 4) AC RMS voltage, 50 Hz, 1min test



Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS 1)	UNITS
V_{FM}	Maximum peak forward voltage	-	-	0.95	I _{FM} =6800A	V
V_{FM}	Maximum peak forward voltage	-	-	1.24	I _{FM} =17000A	V
V_{T0}	Threshold voltage	-	-	0.67	Valid from 2000A to 6000A	V
r _T	Slope resistance	-	-	0.043	Valid from 2000A to 6000A	mΩ
I _{RRM}	Peak reverse current	-	-	100	Rated V _{RRM}	mA
Q_{rr}	Recovered charge	-	3700	4250		μC
Q_{ra}	Recovered charge, 50% Chord	-	3000	-	 I _{TM} =2000A, t _ρ =2000μs, di/dt=10A/μs,	μC
I _{rm}	Reverse recovery current	-	200	-	V _r =100V	Α
t _{rr}	Reverse recovery time, 50% chord	-	30	_		μs
R _{thJC}	Thermal resistance, junction to case	-	-	0.0306		K/W
R_{thCK}	Thermal resistance, case to heatsink	-	-	0.0035		K/W
F ₁	Mounting torque (to heatsink) ²⁾	16	-	23		Nm
F ₂	Mounting torque (to terminals) ³⁾	15	-	20		Nm
W_t	Weight	-	8.14	-		kg

Notes:

- Unless otherwise indicated T_{vj}=190°C.
 Heatsink use M10.
 Terminals use M12.



Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V _{RRM} V	V _{RSM} V	V _R DC V
12	1200	1300	720
15	1500	1600	900

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_{vi} below 25°C.

4.0 Repetitive dv/dt

Standard dv/dt is 1000V/µs.

5.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

6.0 Computer Modelling Parameters

6.1 Diode dissipation calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{{V_{T0}}^2 + 4 \cdot ff^2 \cdot r_T \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_T} \qquad \text{and:} \qquad W_{AV} = \frac{\Delta T}{R_{th}} \\ \Delta T = T_{j \max} - T_C$$

Where $V_{T0} = 0.67V$, $r_T = 0.043m\Omega$.

 R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance						
Conduction Angle 6 phase (60°) 3 phase (120°) ½ wave (180°) d.c.						
Square wave	0.030619	0.030616	0.030614	0.0306		
Sine wave	0.030617	0.030615	0.030611			

Form Factors						
Conduction Angle 6 phase (60°) 3 phase (120°) ½ wave (180°)						
Square wave	2.449	1.732	1.414	1		
Sine wave	2.778	1.879	1.57			



6.2 Calculating diode V_F using ABCD coefficients – For loss calculations

The forward characteristic, I_F vs. V_F, is represented in two ways;

(i) the well established V_{T0} and r_T tangent used for rating purposes and

(ii) a set of constants A, B, C, D, forming the coefficients of the equation for V_F in terms of I_T given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The ABCD constants are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		190°C Coefficients	
Α	0.798634	Α	0.2669197
В	2.80249 ×10 ⁻⁴	В	0.05121623
С	-4.07743×10 ⁻⁶	С	1.71352×10 ⁻⁵
D	4.359019×10 ⁻³	D	1.404316×10 ⁻³

6.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

n= number of terms in the series and

t = duration of heating pulse in seconds.

rt= thermal resistance at time t.

 r_p = Amplitude of p_{th} term.

 τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below:

	D.C. Junction to Case					
Term	Term 1 2 3					
r_p	0.01981779	0.009602212	0.001187377			
$ au_{\mathcal{P}}$	128.6835	15.59559	1.860866			



Curves

Figure 1 – Forward Characteristics of Limit Device

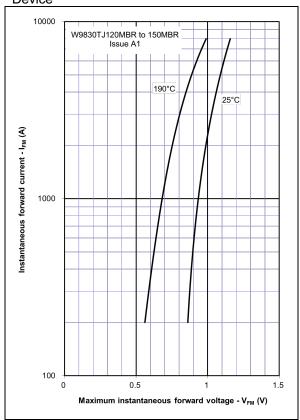


Figure 2 - Transient Thermal Impedance

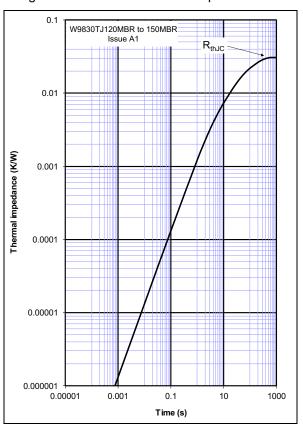


Figure 3 – Forward current vs. Power dissipation

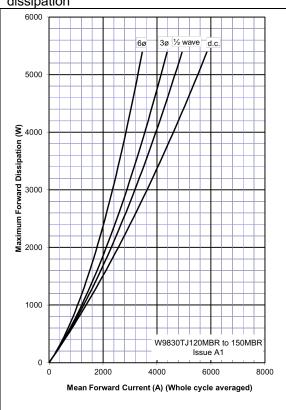


Figure 4 – Forward current vs. Heatsink temperature

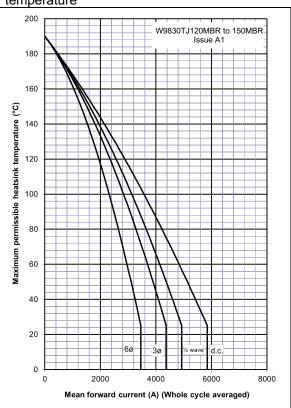




Figure 5 - Total recovered charge, Q_{rr}

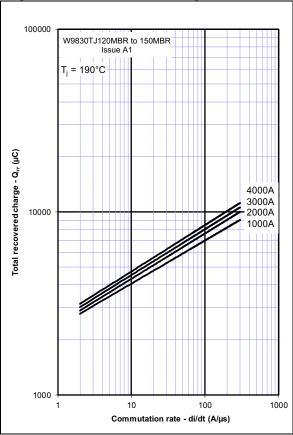


Figure 7 - Peak reverse recovery current, Im

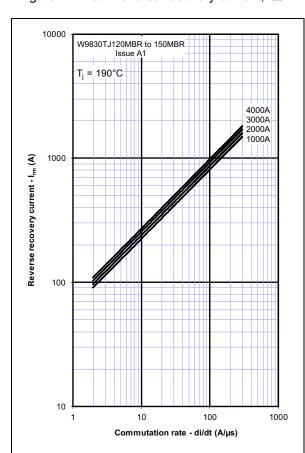


Figure 6 – Recovered charge, Q_{ra} (50% chord)

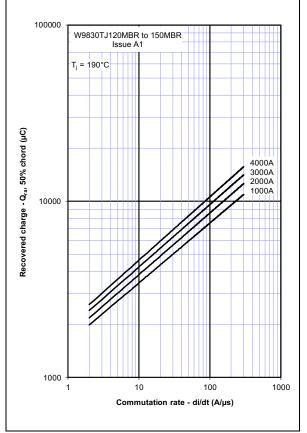
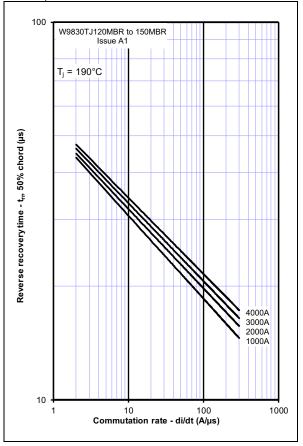
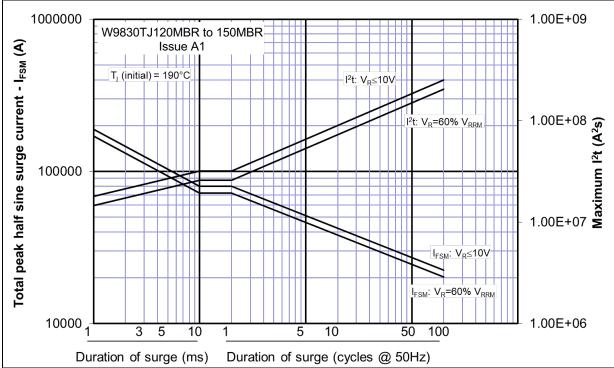


Figure 8 – Maximum recovery time, t_{rr} (50% chord)



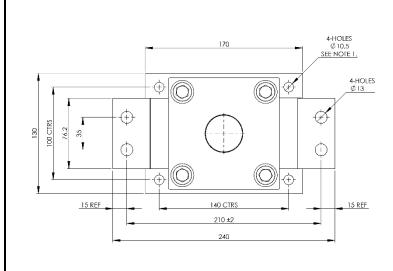






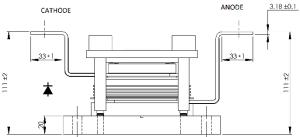


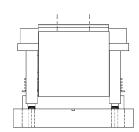
Outline Drawing & Ordering Information



NOTES

1. BASE TO BE FIXED USING M10 BOLTS
TO A TORQUE OF 16-23Nm.





150A132

ORI	DERING INFORMATI	ON (Please	quote 13 digit code as belo	ow)
W9830	TJ	12-15	0	MBR
Fixed Type Code	Fixed Configuration code	Voltage code V _{RRM} x 100	Fixed code	Fixed Version Code

Typical order code: W9830TJ150MBR, 1500V V_{RRM} Rectifier Diode Module

IXYS Semiconductor GmbH

Edisonstraße 15 D-68623 Lampertheim Tel: +49 6206 503-0 Fax: +49 6206 503-627 E-mail: marcom@ixys.de



IXYS UK Westcode Ltd

Langley Park Way, Langley Park, Chippenham, Wiltshire, SN15 1GE. Tel: +44 (0)1249 444524 Fax: +44 (0)1249 659448 E-mail: sales@ixysuk.com

IXYS Corporation

1590 Buckeye Drive Milpitas CA 95035-7418 Tel: +1 (408) 547 9000 Fax: +1 (408) 496 0670 E-mail: sales@ixys.net

www.ixysuk.com

www.ixys.com

IXYS Long Beach, Inc

IXYS Long Beach, Inc 2500 Mira Mar Ave, Long Beach CA 90815

Tel: +1 (562) 296 6584 Fax: +1 (562) 296 6585

E-mail: service@ixyslongbeach.com

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